

N THE CLAIMS:

Please AMEND claims 37-57, and ADD new claims 58 and 59, as follows. For the Examiner's convenience, all claims currently pending in this application have been reproduced below:

1-36. (Canceled)

37. (Currently Amended) An electrostatic ~~sensor~~ sensing apparatus, comprising:
a plurality of detection sections; and
a ~~device arranged to select~~ system which selects at least one detection section from the plurality of detection sections ~~and to calculate a position of an object surface , based on information of a region of an object surface to be detected, and calculates a position of the region,~~ based upon an output of the selected detection section.

38. (Currently Amended) A ~~lithography~~ lithographic system, comprising:
an electrostatic sensor having a plurality of detection sections; and
a controller ~~that~~ which selects at least one detection section from the plurality of detection sections ~~and detects a height of a substrate surface , based on information of a region of a substrate surface to be detected, and calculates a position of the region,~~ based upon an output of the selected detection section.

39.(Currently Amended) ~~The~~ A system according to claim 38, wherein the substrate is a wafer in which a plurality of shot regions to be exposed are arranged, and ~~the controller is arranged to select~~ said controller selects at least one detection section based on a dimension of the shot region.

40. (Currently Amended) ~~The~~ A system according to claim 38, wherein the substrate is a wafer in which a plurality of shot regions to be exposed are arranged, and ~~the controller is arranged to select~~ said controller selects at least one detection section based on a position, of the shot region, in the wafer.

41.(Currently Amended) ~~The~~ A system according to claim 38, wherein the substrate is a wafer in which a plurality of shot regions to be exposed are arranged, and ~~the controller is arranged to select~~ said controller selects at least one detection section based on an arrangement of chip regions in the shot region.

42. (Currently Amended) A device manufacturing method comprising ~~the~~ steps of:

exposing ~~the~~ a substrate using ~~the~~ a lithography system ~~of~~ as recited in claim 38;

. and

developing the exposed substrate.

43. (Currently Amended) A ~~lithography~~ lithographic system, comprising:
a plurality of electrostatic sensors each having a plurality of detection sections;
and
a controller ~~that~~ which selects at least one detection section from each of the
~~plurality~~ plurality of electrostatic sensors ~~and detects a height of a substrate surface , based on~~
information of a region of a substrate surface to be detected, and calculates a position of the
region, based upon outputs of the selected detection sections of the plurality of electrostatic
sensors.

44. (Currently Amended) ~~The~~ A system according to claim 43, wherein the substrate is a
wafer in which a plurality of shot regions to be exposed are arranged, and ~~the controller is~~
~~arranged to select~~ said controller selects at least one detection section from each of the plurality
of electrostatic sensors based on a dimension of the shot region.

45. (Currently Amended) ~~The~~ A system according to claim 43, wherein the substrate is a
wafer in which a plurality of shot regions to be exposed are arranged, and ~~the controller is~~
~~arranged to select~~ said controller selects at least one detection section from each of the plurality
of electrostatic sensors based on a position, of the shot region, in the wafer.

46. (Currently Amended) ~~The~~ A system according to claim 43, wherein the substrate is a wafer in which a plurality of shot regions to be exposed are arranged, and ~~the controller is arranged to select~~ said controller selects at least one detection section from each of the plurality of electrostatic sensors based on an arrangement of chip regions in the shot region.

47. (Currently Amended) A device manufacturing method comprising ~~the~~ steps of:
exposing ~~the~~ a substrate using ~~the lithography system of a lithographic system as recited in claim 43; and~~
developing the exposed substrate.

48. (Currently Amended) A scanning exposure apparatus for exposing a substrate ~~with~~ to a pattern of a mask by scanning the mask and the substrate relative to a slit-shaped exposure beam, ~~the~~ said exposure apparatus comprising:

an electrostatic sensor having a plurality of detection sections arranged in a direction perpendicular to a scanning direction of the mask and the substrate; and

a controller ~~that~~ which selects at least one detection section from the plurality of detection sections ~~and detects a height of a substrate surface , based on information of a region of a surface of the substrate to be detected, and calculates a position of the region~~ based upon an output of the selected detection section.

49. (Currently Amended) ~~The~~ An apparatus according to claim 48, wherein the substrate is a wafer in which a plurality of shot regions to be exposed are arranged, and ~~the controller is further arranged to select~~ said controller selects at least one detection section based on a dimension of the shot region.

50. (Currently Amended) ~~The~~ An apparatus according to claim 48, wherein the substrate is a wafer in which a plurality of shot regions to be exposed are arranged, and ~~the controller is arranged to select~~ said controller selects at least one detection section based on a position, of the shot region, in the wafer.

51. (Currently Amended) ~~The~~ An apparatus according to claim 48, wherein the substrate is a wafer in which a plurality of shot regions to be exposed are arranged, and ~~the controller is arranged to select~~ said controller selects at least one detection section based on an arrangement of chip regions in the shot region.

52. (Currently Amended) A device manufacturing method comprising ~~the~~ steps of:
 exposing ~~the~~ a substrate using ~~the~~ a scanning exposure apparatus ~~of~~ as recited in
claim 48; and
 developing the exposed substrate.

53. (Currently Amended) A scanning exposure apparatus for exposing a substrate ~~with~~ to a pattern of a mask by scanning the mask and the substrate relative to a slit-shaped exposure beam, ~~the~~ the exposure apparatus comprising:

a plurality of electrostatic sensors ~~arranged in a scanning direction of the mask and the substrate, wherein each of the plurality of electrostatic sensors has~~ each having a plurality of detection sections arranged in a direction perpendicular to ~~the~~ a scanning direction of the mask and the substrate; and

a controller ~~that~~ which selects at least one detection section from each of the plurality of electrostatic sensors ~~and detects a height of a substrate surface~~ , based on information of a region of a surface of the substrate to be detected, and calculates a position of the region, based upon outputs of the selected detection sections of the plurality of electrostatic sensors.

54. (Currently Amended) ~~The~~ An apparatus according to claim 53, wherein the substrate is a wafer in which a plurality of shot regions to be exposed are arranged, and ~~the controller is arranged to select~~ said controller selects at least one detection section from each of the plurality of electrostatic sensors based on a dimension of the shot region.

55. (Currently Amended) ~~The~~ An apparatus according to claim 53, wherein the substrate is a wafer in which a plurality of shot regions to be exposed are arranged, and ~~the controller is arranged to select~~ said controller selects at least one detection section from each of the plurality of electrostatic sensors based on a position, of the shot region, in the wafer.

56. (Currently Amended) ~~The~~ An apparatus according to claim 53, wherein the substrate is a wafer in which a plurality of shot regions to be exposed are arranged, and ~~the controller is arranged to select~~ said controller selects at least one detection section from each of the plurality of electrostatic sensors based on an arrangement of chip regions in the shot region.

57. (Currently Amended) A device manufacturing method comprising ~~the~~ steps of:
 exposing ~~the~~ a substrate using ~~the~~ a scanning exposure apparatus ~~of~~ as recited in
claim 53; and
 developing the exposed substrate.

58. (New) An apparatus according to claim 48, wherein the plurality of electrostatic sensors are arranged at each of a plurality of positions in a scanning direction of the mask and the substrate.

59. (New) An apparatus according to claim 53, wherein the plurality of electrostatic sensors are arranged at each of a plurality of positions in a scanning direction of the mask and the substrate.